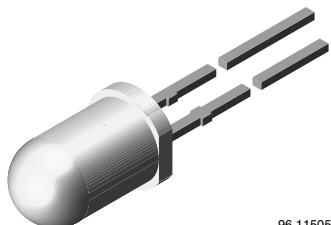


High Power Infrared Emitting Diode, 940 nm, GaAlAs/GaAs



96 11505

DESCRIPTION

TSAL5100 is an infrared, 940 nm emitting diode in GaAlAs/GaAs technology with high radiant power, molded in a blue-gray plastic package.

FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm): $\varnothing$ 5
- Leads with stand-off
- Peak wavelength: $\lambda_p = 940$ nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: $\varphi = \pm 10^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Infrared remote control units with high power requirements
- Free air transmission systems
- Infrared source for optical counters and card readers
- IR source for smoke detectors
- Smoke-automatic fire detectors

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	φ (deg)	λ_p (nm)	t_r (ns)
TSAL5100	130	± 10	940	800

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSAL5100	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5$, $t_p = 100$ μ s	I_{FM}	200	mA
Surge forward current	$t_p = 100$ μ s	I_{FSM}	1.5	A
Power dissipation		P_V	160	mW
Junction temperature		T_j	100	$^\circ$ C
Operating temperature range		T_{amb}	- 40 to + 85	$^\circ$ C
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ$ C
Soldering temperature	$t \leq 5$ s, 2 mm from case	T_{sd}	260	$^\circ$ C
Thermal resistance junction/ambient	J-STD-051, leads 7 mm soldered on PCB	R_{thJA}	230	K/W

Note

$T_{amb} = 25$ $^\circ$ C, unless otherwise specified

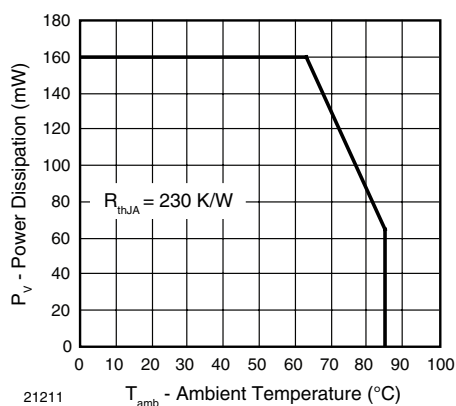


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

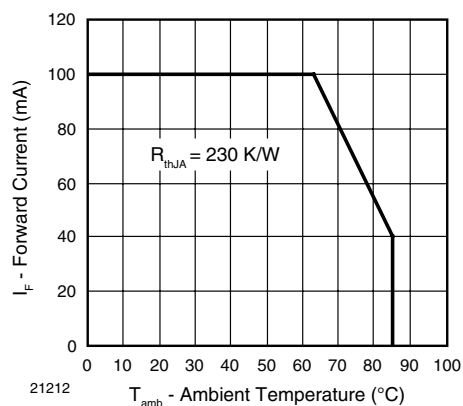


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$	V_F		1.35	1.6	V
	$I_F = 1 \text{ A}$, $t_p = 100 \mu\text{s}$	V_F		2.6	3	V
Temperature coefficient of V_F	$I_F = 1 \text{ mA}$	TK_{V_F}		- 1.8		mV/K
Reverse current	$V_R = 5 \text{ V}$	I_R			10	μA
Junction capacitance	$V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$, $E = 0$	C_j		25		pF
Radiant intensity	$I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$	I_e	80	130	400	mW/sr
	$I_F = 1 \text{ A}$, $t_p = 100 \mu\text{s}$	I_e	650	1000		mW/sr
Radiant power	$I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$	ϕ_e		35		mW
Temperature coefficient of ϕ_e	$I_F = 20 \text{ mA}$	TK_{ϕ_e}		- 0.6		%/K
Angle of half intensity		φ		± 10		deg
Peak wavelength	$I_F = 100 \text{ mA}$	λ_p		940		nm
Spectral bandwidth	$I_F = 100 \text{ mA}$	$\Delta\lambda$		50		nm
Temperature coefficient of λ_p	$I_F = 100 \text{ mA}$	TK_{λ_p}		0.2		nm/K
Rise time	$I_F = 100 \text{ mA}$	t_r		800		ns
Fall time	$I_F = 100 \text{ mA}$	t_f		800		ns
Virtual source diameter	method: 63 % encircled energy	d		3.7		mm

Note

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

BASIC CHARACTERISTICS

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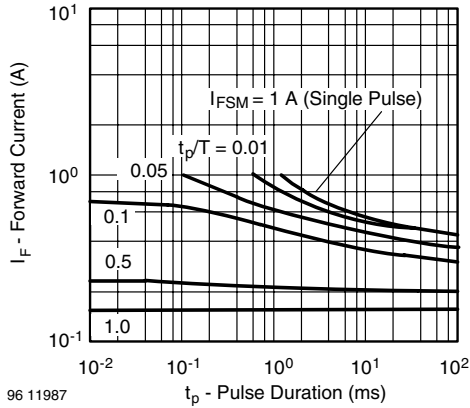


Fig. 3 - Pulse Forward Current vs. Pulse Duration

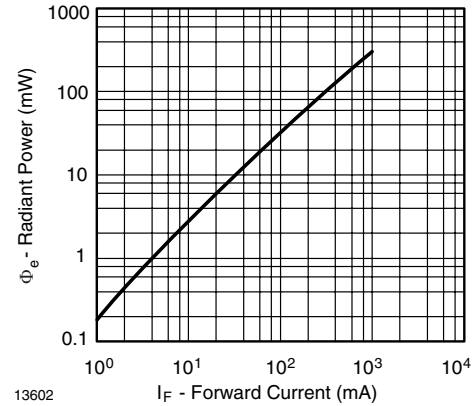


Fig. 6 - Radiant Power vs. Forward Current

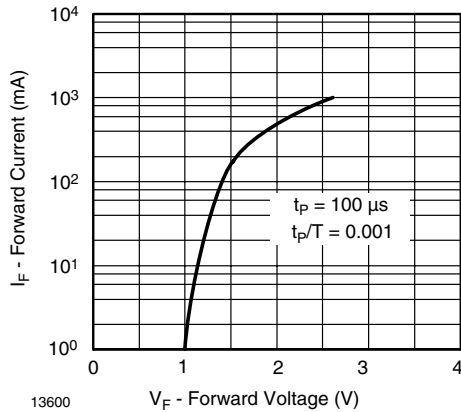


Fig. 4 - Forward Current vs. Forward Voltage

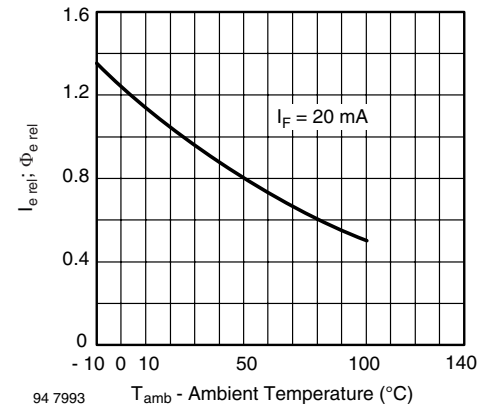


Fig. 7 - Rel. Radiant Intensity/Power vs. Ambient Temperature

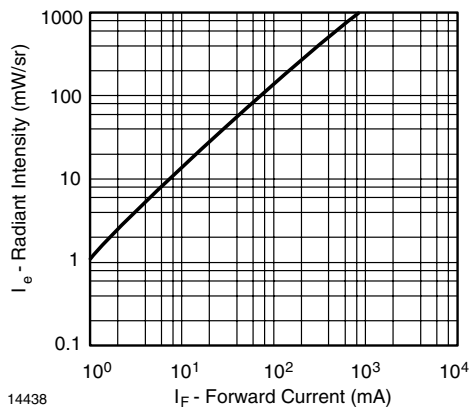


Fig. 5 - Radiant Intensity vs. Forward Current

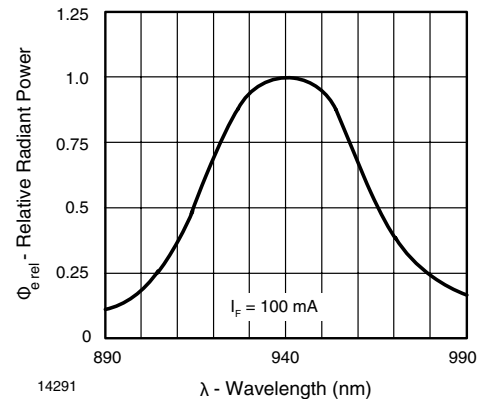


Fig. 8 - Relative Radiant Power vs. Wavelength

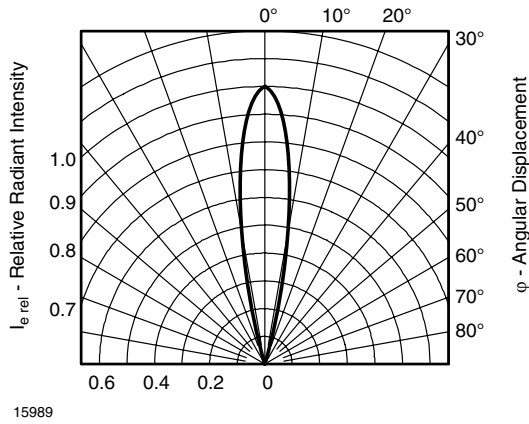
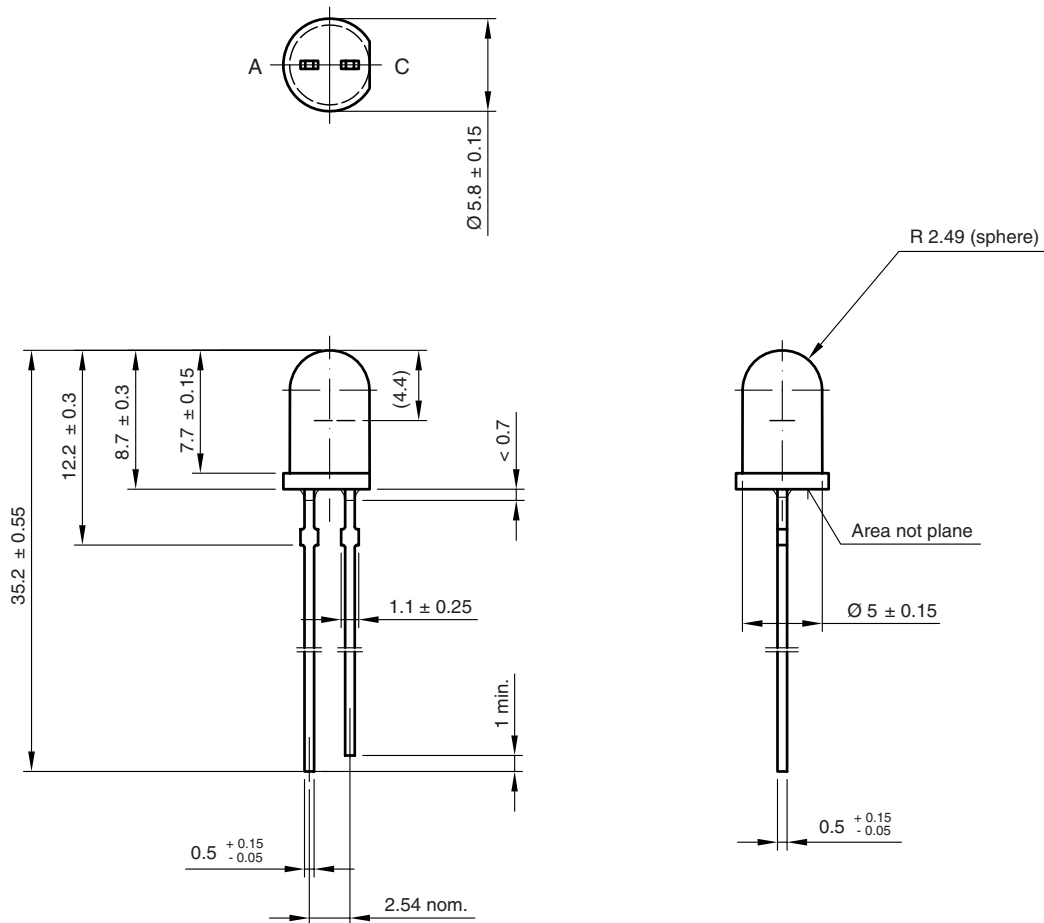


Fig. 9 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



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